

N-Channel Silicon MOSFET

# HB60N20W General-Purpose Switching Device Applications

## Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

## Specifications

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±12	V
Drain Current (DC)	I <sub>D</sub>		3.5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	14	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm²×0.8mm)	1	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1.8A	2.8	4.8		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =1.8A, V <sub>GS</sub> =4V		55	72	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V		70	98	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, f=1MHz		415		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =10V, f=1MHz		55		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		11		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		65		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		54		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		61		ns

Marking : ZG

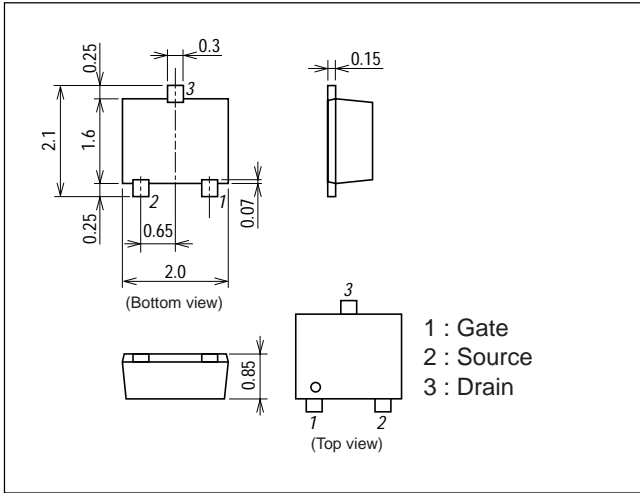
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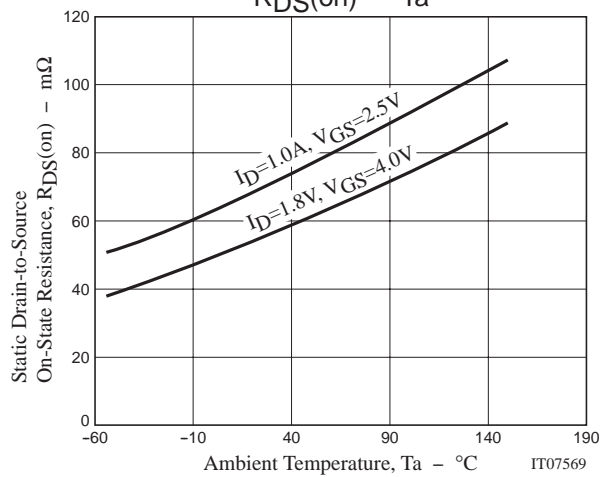
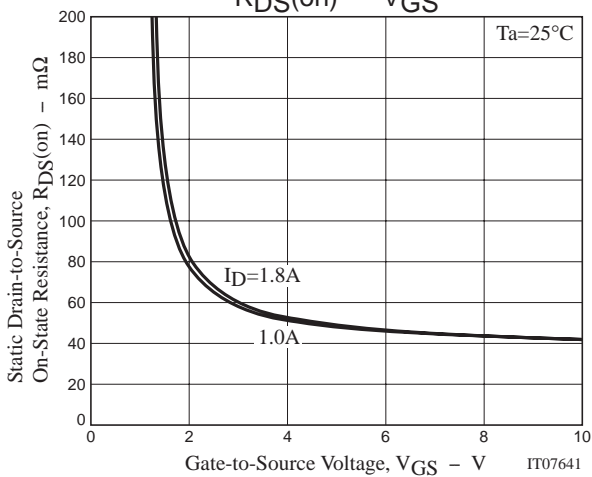
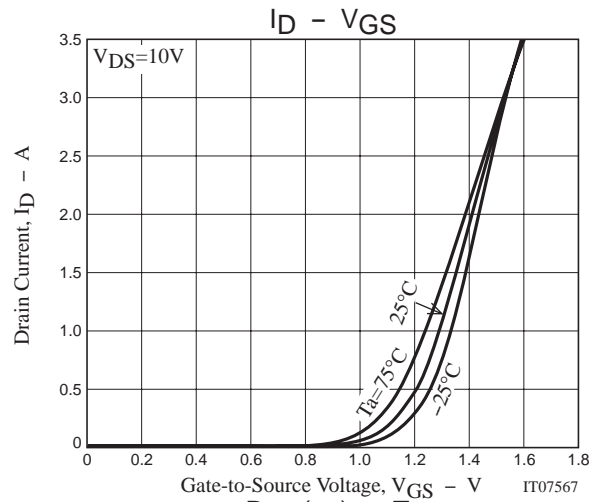
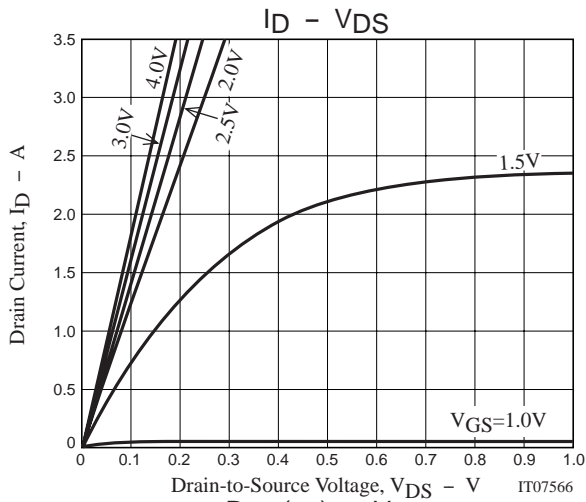
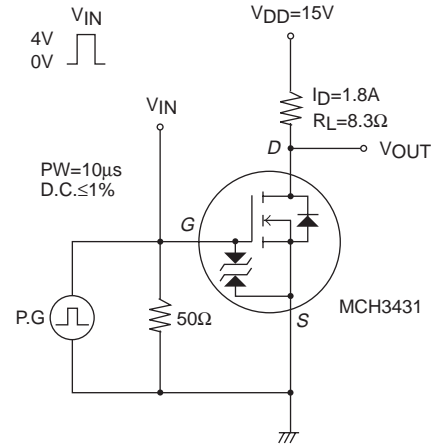
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	$V_{DS}=10V, V_{GS}=4V, I_D=3.5A$		5.1		nC
Gate-to-Source Charge	Qgs	$V_{DS}=10V, V_{GS}=4V, I_D=3.5A$		0.95		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=10V, V_{GS}=4V, I_D=3.5A$		1.4		nC
Diode Forward Voltage	$V_{SD}$	$I_S=3.5A, V_{GS}=0$		0.87	1.2	V

## Package Dimensions

unit : mm



## Switching Time Test Circuit



# HB60N20W

